

Jean-Louis J-L Lazzari

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

92
papers

836
citations

16
h-index

24
g-index

101
ext. papers

934
ext. citations

2.7
avg, IF

3.56
L-index

#	Paper	IF	Citations
92	Modelization of electrical and optical characteristics of short-wave infrared type I InGaAsBi/InGaAs/InP quantum wells p-i-n detector. <i>Physica Scripta</i> , 2021 , 96, 035802	2.6	
91	Energy band gap tuning in Te-doped WS ₂ /WSe ₂ heterostructures. <i>Journal of Materials Science</i> , 2020 , 55, 9695-9702	4.3	4
90	Study of n-WO ₃ /p-porous silicon structures for gas-sensing applications. <i>Journal of Materials Science: Materials in Electronics</i> , 2020 , 31, 7862-7870	2.1	3
89	Electronic Properties of WS ₂ /WSe ₂ Heterostructure Containing Te Impurity: The Role of Substituting Position. <i>International Journal of Nanoscience</i> , 2019 , 18, 1940007	0.6	0
88	Elaboration and characterization of CuInSe ₂ thin films using one-step electrodeposition method on silicon substrate for photovoltaic application. <i>Materials Research Express</i> , 2018 , 5, 016414	1.7	6
87	Enhancement of physical properties of stain-etched porous silicon by integration of WO ₃ nanoparticles. <i>Thin Solid Films</i> , 2018 , 645, 51-56	2.2	7
86	Study of WO ₃ -decorated porous silicon and Al ₂ O ₃ -ALD encapsulation. <i>Journal of Materials Science: Materials in Electronics</i> , 2018 , 29, 17731-17736	2.1	3
85	Multiscale in modelling and validation for solar photovoltaics. <i>EPJ Photovoltaics</i> , 2018 , 9, 10	0.7	5
84	Contribution of a single quantum dots layer in intermediate band solar cells: A capacitance analysis. <i>Solar Energy Materials and Solar Cells</i> , 2017 , 159, 633-639	6.4	7
83	Releasing confined holes from type-II quantum dots by inelastic scattering with hot photoelectrons. <i>Solar Energy Materials and Solar Cells</i> , 2016 , 144, 767-774	6.4	3
82	Self-consistent vertical transport calculations in Al _x Ga _{1-x} N/GaN based resonant tunneling diode. <i>Superlattices and Microstructures</i> , 2016 , 91, 37-50	2.8	8
81	Low-defect metamorphic Si (Ge) epilayers on Si (001) with a buried template of nanocavities for multiple-junction solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2016 , 144, 775-780	6.4	4
80	Composition dependence of the band offsets in wurtzite nitride-based heterojunctions. <i>Materials Science in Semiconductor Processing</i> , 2016 , 41, 121-131	4.3	2
79	Stark shift of the absorption spectra in Ge/Ge _{1-x} Sn _x /Ge type-I single QW cell for mid-wavelength infra-red modulators. <i>Superlattices and Microstructures</i> , 2015 , 85, 629-637	2.8	5
78	Performance evaluation of high-detectivity p-i-n infrared photodetector based on compressively-strained Ge _{0.964} Sn _{0.036} /Ge multiple quantum wells by quantum modelling. <i>Semiconductor Science and Technology</i> , 2015 , 30, 085016	1.8	12
77	Resonant tunneling transport in Al _z Ga _{1-z} N/In _x Ga _{1-x} N/Al _z Ga _{1-z} N/In _y Ga _{1-y} N quantum structures. <i>Journal Physics D: Applied Physics</i> , 2015 , 48, 385102	3	6
76	Impact of spatial separation of type-II GaSb quantum dots from the depletion region on the conversion efficiency limit of GaAs solar cells. <i>Progress in Photovoltaics: Research and Applications</i> , 2015 , 23, 1003-1016	6.8	8

75	Direct band gap In _x Ga _{1-x} As/Ge type II strained quantum wells for short-wave infrared p-i-n photodetector. <i>Optical Materials</i> , 2015 , 46, 472-480	3.3	1
74	Band gap modifications of two-dimensional defected MoS ₂ . <i>International Journal of Nanotechnology</i> , 2015 , 12, 654	1.5	7
73	Theoretical study of defect impact on two-dimensional MoS ₂ . <i>Journal of Semiconductors</i> , 2015 , 36, 122002	0.2	35
72	Electron transport through cubic InGaN/AlGaIn resonant tunneling diodes. <i>Computer Physics Communications</i> , 2014 , 185, 3119-3126	4.2	9
71	Magnetic properties of Al _{1-x} B _x IVC ₂ V chalcopyrite semiconductors doped with 3d-elements. <i>Physica Status Solidi (B): Basic Research</i> , 2014 , 251, 1007-1019	1.3	5
70	Band engineering and absorption spectra in compressively strained Ge _{0.92} Sn _{0.08} /Ge (001) double quantum well for infrared photodetection. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 1561-1565		9
69	Wave-function engineering and absorption spectra in Si _{0.16} Ge _{0.84} /Ge _{0.94} Sn _{0.06} /Si _{0.16} Ge _{0.84} strained on relaxed Si _{0.10} Ge _{0.90} type I quantum well. <i>Journal of Applied Physics</i> , 2014 , 115, 033109	2.5	16
68	Modelling of the Quantum Transport in Strained Si/SiGe/Si Superlattices Based P-i-n Infrared Photodetectors for 1.3 - 1.55 μ m Optical Communication. <i>Modeling and Numerical Simulation of Material Science</i> , 2014 , 04, 37-52	0.7	3
67	Intersubband transitions in quantum well mid-infrared photodetectors. <i>Infrared Physics and Technology</i> , 2013 , 60, 137-144	2.7	15
66	Computation of the electronic structure and direct-gap absorption spectra in Ge-rich Si _{1-x} Gex/Ge/Si _{1-x} Gex type-I quantum wells. <i>European Physical Journal B</i> , 2013 , 86, 1	1.2	7
65	Modification of band alignment at interface of AlyGa _{1-y} Sb/AlxGa _{1-x} As type-II quantum dots by concentrated sunlight in intermediate-band solar cells with separated absorption and depletion regions 2013 ,		1
64	Si/Si _{1-x} Gex/Si-based quantum wells infrared photodetector operating at 1.55 μ m. <i>Superlattices and Microstructures</i> , 2012 , 52, 901-912	2.8	1
63	Ab initio modeling of the structural, electronic, and optical properties of Al _{1-x} B _x IVC ₂ V semiconductors. <i>Physical Review B</i> , 2012 , 85,	3.3	101
62	Mn concentration and quantum size effects on spin-polarized transport through CdMnTe based magnetic resonant tunneling diode. <i>Journal of Nanoscience and Nanotechnology</i> , 2012 , 12, 8791-6	1.3	1
61	A multi-color quantum well photodetector for mid- and long-wavelength infrared detection. <i>Semiconductor Science and Technology</i> , 2011 , 26, 125019	1.8	9
60	A theoretical study of band structure properties for III ν nitrides quantum wells. <i>Superlattices and Microstructures</i> , 2011 , 50, 277-288	2.8	1
59	Different architectures of relaxed Si _{1-x} Gex/Si pseudo-substrates grown by low-pressure chemical vapor deposition: Structural and morphological characteristics. <i>Journal of Crystal Growth</i> , 2011 , 328, 18-24	1.6	7
58	Electrical field and temperature effects in 2D-2D resonant tunneling diodes based on cubic InGaIn/AlGaIn. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 1544-1547		1

57	Spin polarization and spin-dependent transmittance in $\text{In}_{1-x}\text{Ga}_x\text{As}_{1-y}\text{Sb}_y$ diluted magnetic semiconductor heterostructure. <i>Journal of Magnetism and Magnetic Materials</i> , 2011 , 323, 334-339	2.8	
56	Surface morphology and structure of ultra-thin magnesium oxide grown on (100) silicon by atomic layer deposition oxidation. <i>Thin Solid Films</i> , 2011 , 519, 6302-6306	2.2	8
55	Engineering of $\text{Ga}_{1-x}\text{In}_x\text{As}_y\text{Sb}_{1-y}$ /GaSb quantum well for III-V based devices emitting near 2.7 μm . <i>IOP Conference Series: Materials Science and Engineering</i> , 2010 , 13, 012005	0.4	
54	Inter-diffusion of cobalt and silicon through an ultra thin aluminum oxide layer. <i>Applied Surface Science</i> , 2010 , 256, 2731-2734	6.7	11
53	Interfacial solid phase reactions in cobalt/aluminum oxide/silicon(001) system. <i>Thin Solid Films</i> , 2010 , 518, 5992-5994	2.2	11
52	A theoretical study of laser structures based on dilute-nitride InAsN for mid-infrared operation. <i>Semiconductor Science and Technology</i> , 2009 , 24, 085010	1.8	10
51	Electronic and magnetic properties of Mn-doped BeSiAs_2 and BeGeAs_2 compounds. <i>Journal of Physics Condensed Matter</i> , 2009 , 21, 045507	1.8	15
50	Computer simulation of electronic and magnetic properties of ternary chalcopyrites doped with transition metals 2008 ,		4
49	InAsN/GaSb/InAsN MQW quantum well laser for mid-infrared emission: from electronic structure to threshold current density calculations. <i>Journal Physics D: Applied Physics</i> , 2008 , 41, 215106	3	11
48	Structural, electronic and optical properties of IIIV_2 compounds (II = Be, Zn; IV = Si, Ge). <i>Physica Status Solidi (B): Basic Research</i> , 2008 , 245, 142-148	1.3	26
47	Nitrogen effect on optical gain and radiative current density for mid-infrared InAs(N)/GaSb/InAs(N) quantum-well laser. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008 , 40, 489-493	3	8
46	Simulation of p-n heterojunctions built on strain-compensated $\text{Si}/\text{Si}_{0.40}\text{Ge}_{0.60}/\text{Si}$ multiple quantum wells for photodetection near 1.55 μm . <i>Thin Solid Films</i> , 2008 , 517, 388-390	2.2	1
45	Optical gain calculation of mid-infrared InAsN/GaSb quantum-well laser for tunable absorption spectroscopy applications. <i>Materials Science and Engineering C</i> , 2008 , 28, 751-754	8.3	3
44	Coulomb interaction of electron gas in MQWs $\text{Si}/\text{Si}_{1-x}\text{Ge}_x/\text{Si}$. <i>Materials Science and Engineering C</i> , 2008 , 28, 939-942	8.3	1
43	Carrier Concentration Control of GaSb/GaInAsSb System. <i>AIP Conference Proceedings</i> , 2007 ,	0	1
42	Controlled growth of aluminum oxide thin films on hydrogen terminated $\text{Si}(001)$ surface. <i>Journal of Crystal Growth</i> , 2007 , 305, 26-29	1.6	16
41	A novel quantum laser structure based on InAsN/GaSb system. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 592-594		
40	Resonant tunneling versus thermally activated transport through strained $\text{Si}_{1-x}\text{Ge}_x\text{Bi}_y\text{Si}_{1-y}\text{Ge}_x$ quantum wells. <i>Physical Review B</i> , 2007 , 75,	3.3	8

39	Growth of magnetic tunnel junctions on Si(001) substrates. <i>Thin Solid Films</i> , 2007 , 515, 6501-6506	2.2	2
38	Nanocavity Buffer Induced by Gas Ion Implantation in Silicon Substrate for Strain Relaxation of Heteroepitaxial Si _{1-x} Gex/Si Thin Layers. <i>Materials Research Society Symposia Proceedings</i> , 2007 , 994, 1		2
37	Prospects on Mn-doped ZnGeP ₂ for spintronics. <i>Microelectronics Reliability</i> , 2006 , 46, 1747-1749	1.2	11
36	Field effect on electron-hole recombination in Si/Si _{1-x} Gex/Si quantum wells having a W-like type II potential profile. <i>Materials Science and Engineering C</i> , 2006 , 26, 214-217	8.3	
35	Modeling of the Stark effect in strained Ge _{0.6} Si _{0.4} /Si/Ge _{0.6} Si _{0.4} resonant tunneling diodes with graded GexSi _{1-x} (0.3. <i>Materials Science in Semiconductor Processing</i> , 2006 , 9, 737-740	4.3	
34	Induced electrostatic confinement of electron gas in W-designed strain-compensated Si/Si _{1-x} Gex/Si type-II quantum wells. <i>Journal of Luminescence</i> , 2006 , 121, 421-425	3.8	1
33	Field effect on optical recombination in Si/SiGe quantum heterostructures having U, W and M type II potential designs. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005 , 124-125, 470-474	3.1	
32	Wave function engineering in W designed strained-compensated Si/Si _{1-x} Gex/Si type II quantum wells for 1.55 μ m optical properties. <i>Optical Materials</i> , 2005 , 27, 859-863	3.3	11
31	Strain-balanced Si _{1-x} Gex/Si type II quantum wells for 1.55 μ m detection and emission. <i>European Physical Journal B</i> , 2005 , 48, 151-156	1.2	17
30	Modelling of visible and near infrared wavelength quantum well devices made of zinc-blende In _x Ga _{1-x} N. <i>Journal of Physics Condensed Matter</i> , 2004 , 16, 511-519	1.8	8
29	Band offset calculations applied to III _V nitride quantum well device engineering. <i>Superlattices and Microstructures</i> , 2004 , 36, 799-806	2.8	4
28	Electronic structure calculations for Si/Si _{1-x} Gex multi-quantum well devices. <i>Materials Science and Engineering C</i> , 2003 , 23, 959-963	8.3	
27	Electric field effect on the spatially separated electron-hole recombination in an Si/Si _{1-x} Gex resonant tunneling heterostructure. <i>Physica B: Condensed Matter</i> , 2002 , 322, 37-41	2.8	4
26	Electronic structure and optical properties of Si _{1-x} Gex alloys. <i>Physica B: Condensed Matter</i> , 2002 , 322, 225-235	2.8	11
25	Stark effect modeling in strained n-type Si/Si _{1-x} Gex resonant tunneling heterostructures. <i>Journal of Applied Physics</i> , 2002 , 91, 9170-9176	2.5	24
24	Chemical vapor deposition of silicon-germanium heterostructures. <i>Journal of Crystal Growth</i> , 2000 , 216, 171-184	1.6	27
23	Investigation of Si/SiGe heterostructure material using non-destructive optical techniques. <i>Thin Solid Films</i> , 2000 , 364, 75-79	2.2	1
22	Temperature and excitation power dependencies of the photoluminescence of planar and vertically self-organized Si _{0.7} Ge _{0.3} /Si strained superlattices. <i>Thin Solid Films</i> , 2000 , 380, 130-133	2.2	5

21	Structural characterization of Si _{1-x} Gex/Si strained superlattices and relaxed virtual substrates grown by chemical vapor deposition. <i>Applied Surface Science</i> , 2000 , 164, 35-41	6.7	7
20	Interfacial deep-level defects as probes for ultrathin InAs insertions in GaAs. <i>Journal of Crystal Growth</i> , 1999 , 201-202, 267-270	1.6	3
19	Silicon quantum integrated circuits – an attempt to fabricate silicon-based quantum devices using CMOS fabrication techniques. <i>Thin Solid Films</i> , 1998 , 336, 130-136	2.2	15
18	Deep and shallow electronic states at ultrathin InAs insertions in GaAs investigated by capacitance spectroscopy. <i>Journal of Applied Physics</i> , 1998 , 84, 6135-6140	2.5	25
17	Electroluminescence of GaInSb/GaSb strained single quantum well structures grown by molecular beam epitaxy. <i>Semiconductor Science and Technology</i> , 1996 , 11, 1185-1188	1.8	20
16	High sensitivity 2.5 μ m photodiodes with metastable GaInAsSb absorbing layer. <i>Solid-State Electronics</i> , 1996 , 39, 39-41	1.7	3
15	X, I, and II lines in low temperature photoluminescence spectra of Al _{0.47} Ga _{0.53} As _{0.035} Sb _{0.965} alloys. <i>Physica Status Solidi (B): Basic Research</i> , 1996 , 196, 453-460	1.3	
14	Does the 1.25 eV Luminescence of Coherently Strained InGaAs Insertions in GaAs Originate from Quantum Dots?. <i>Materials Research Society Symposia Proceedings</i> , 1995 , 417, 199		1
13	High-power low-threshold Ga _{0.88} In _{0.12} As _{0.10} Sb _{0.90} / Al _{0.47} Ga _{0.53} As _{0.04} Sb _{0.96} double heterostructure lasers grown by liquid phase epitaxy. <i>Electronics Letters</i> , 1994 , 30, 312-314	1.1	4
12	High temperature operation of GaInAsSb/AlGaAsSb double-heterostructure lasers emitting near 2.1 μ m. <i>Applied Physics Letters</i> , 1994 , 65, 616-617	3.4	16
11	Electrical determination of band offsets in a p-Ga _{0.77} In _{0.23} As _{0.20} Sb _{0.80} / n-GaSb type-II heterojunction. <i>Journal of Applied Physics</i> , 1993 , 73, 2360-2363	2.5	13
10	Optical properties and fluctuations of composition in Ga _{0.77} In _{0.23} As _{0.19} Sb _{0.81} alloys. <i>Solid State Communications</i> , 1993 , 85, 177-181	1.6	3
9	Critical layer thickness in AlGaAsSbGaSb heterostructures determined by X-ray diffraction. <i>Journal of Crystal Growth</i> , 1993 , 130, 96-100	1.6	11
8	Low Temperature Photoluminescence Spectra of Ga _{0.77} In _{0.23} As _{0.19} Sb _{0.81} Compounds. <i>Physica Status Solidi (B): Basic Research</i> , 1993 , 180, K87-K91	1.3	1
7	Determination of electrical and optical parameters of Ga _{1-x} In _x As _y Sb _{1-y} and Ga _{1-x} Al _x As _y Sb _{1-y} thin layers grown on GaSb substrates by IR reflectivity. <i>Thin Solid Films</i> , 1992 , 221, 196-202	2.2	9
6	Liquid phase epitaxial growth of AlGaAsSb on GaSb. <i>Journal of Crystal Growth</i> , 1992 , 123, 465-478	1.6	19
5	Liquid phase epitaxy and characterization of InAs _{1-x-y} Sb _x P _y on (100) InAs. <i>Journal of Crystal Growth</i> , 1992 , 121, 463-472	1.6	20
4	Growth by liquid phase epitaxy and characterization of GaInAsSb and InAsSbP alloys for mid-infrared applications (2-3 μ m) 1991 ,		8

3	Growth limitations by the miscibility gap in liquid phase epitaxy of Ga _{1-x} In _x As _y Sb _{1-y} on GaSb. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1991 , 9, 125-128	3.1	26
2	GaInAsSb/GaSb pn photodiodes for detection to 2.4 μ m. <i>Electronics Letters</i> , 1991 , 27, 1237	1.1	24
1	2.5 μ m GaInAsSb lattice-matched to GaSb by liquid phase epitaxy. <i>Journal of Applied Physics</i> , 1990 , 68, 5936-5938	2.5	33